



STP13N95K3, STF13N95K3 STW13N95K3

N-channel 950 V, 0.68 Ω , 10 A, TO-220, TO-220FP, TO-247
SuperMESH3™ Power MOSFET

Preliminary data

Features

Type	V _{DSS}	R _{DS(on)} max	I _D	P _w
STP13N95K3	950 V	< 0.85 Ω	10 A	190 W
STF13N95K3	950 V	< 0.85 Ω	10 A	40 W
STW13N95K3	950 V	< 0.85 Ω	10 A	190 W

- 100% avalanche tested
- Extremely large avalanche performance
- Gate charge minimized
- Very low intrinsic capacitances
- Zener-protected

Application

- Switching applications

Description

The new SuperMESH3™ series of Power MOSFETS is the result of the fine-tuning of ST's well-established strip-based PowerMESH™ layout with a new optimized vertical structure. The innovative design offer significantly reduced on-resistance, exceptional dynamic performance and very large avalanche capability, making the device suitable for the most demanding applications.

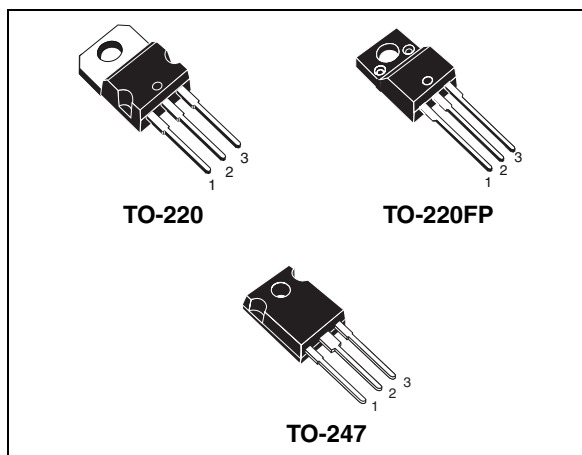


Figure 1. Internal schematic diagram

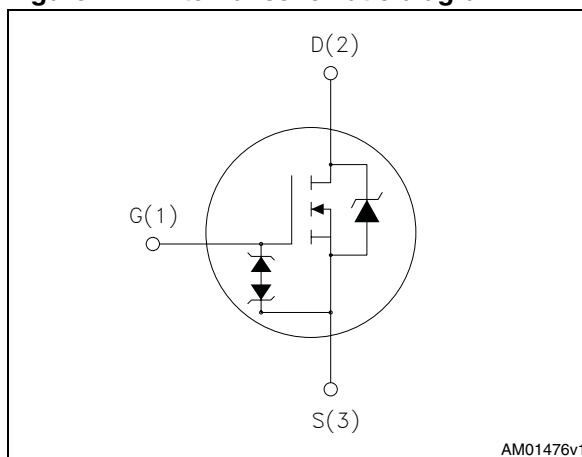


Table 1. Device summary

Order code	Marking	Package	Packaging
STF13N95K3	13N95K3	TO-220FP	Tube
STP13N95K3	13N95K3	TO-220	Tube
STW13N95K3	13N95K3	TO-247	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value			Unit
		TO-220	TO-220FP	TO-247	
V_{GS}	Gate- source voltage	30			V
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	10	10 ⁽¹⁾	10	A
I_D	Drain current (continuous) at $T_C = 100\text{ °C}$	6.3	6.3 ⁽¹⁾	6.3	A
$I_{DM}^{(2)}$	Drain current (pulsed)	40	40 ⁽¹⁾	40	A
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	190	40	190	W
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J max)	13			A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	TBD			mJ
$dv/dt^{(3)}$	Peak diode recovery voltage slope	6			V/ns
V_{ISO}	Insulation withstand voltage (AC)		2500		
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 150			°C

- Limited only by maximum temperature allowed
- Pulse width limited by safe operating area
- $I_{SD} \leq 10\text{ A}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, peak $V_{DS} \leq V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value			Unit
		TO-220	TO-220FP	TO-247	
$R_{thj-case}$	Thermal resistance junction-case max	0.66	3.13	0.66	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.50		50.00	°C/W
T_J	Maximum lead temperature for soldering purpose	300			°C/W

2 Electrical characteristics

(T_{case} = 25°C unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1 mA, V _{GS} = 0	950			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = Max rating V _{DS} = Max rating, T _C = 125 °C			1 50	μA μA
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 20 V; V _{DS} = 0			10	μA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 100 μA	3	4	5	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10 V, I _D = 5 A		0.68	0.85	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g _{fs} ⁽¹⁾	Forward transconductance	V _{DS} = 15 V, I _D = 13 A	-	TBD	-	S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} = 100 V, f = 1 MHz, V _{GS} = 0	-	1700 178 2	-	pF pF pF
C _{o(tr)} ⁽²⁾	Equivalent capacitance time related	V _{DS} = 0 to 760 V, V _{GS} = 0	-	TBD	-	pF
C _{o(er)} ⁽³⁾	Equivalent capacitance energy related	V _{DS} = 0 to 760 V, V _{GS} = 0	-	TBD	-	pF
R _g	Gate input resistance	f = 1 MHz open drain	-	2	-	Ω
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V _{DD} = 760 V, I _D = 10 A, V _{GS} = 10 V (see Figure 3)	-	49 TBD TBD	-	nC nC nC

1. Pulsed: Pulse duration = 300 μs, duty cycle 1.5%
2. C_{oss eq.} time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
3. C_{oss eq.} energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 475 \text{ V}$, $I_D = 5 \text{ A}$, $R_G = 4.7 \Omega$, $V_{GS} = 10 \text{ V}$ (see Figure 2)	-	TBD	-	ns
t_r	Rise time			TBD		ns
$t_{d(off)}$	Turn-off-delay time			TBD		ns
t_f	Fall time			TBD		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current		-		10	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				40	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 10 \text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 10 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (see Figure 4)	-	TBD		ns
Q_{rr}	Reverse recovery charge			TBD		μC
I_{RRM}	Reverse recovery current			TBD		A
t_{rr}	Reverse recovery time	$I_{SD} = 10 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ $T_J = 150 \text{ }^\circ\text{C}$ (see Figure 4)	-	TBD		ns
Q_{rr}	Reverse recovery charge			TBD		μC
I_{RRM}	Reverse recovery current			TBD		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 8. Gate-source Zener diode

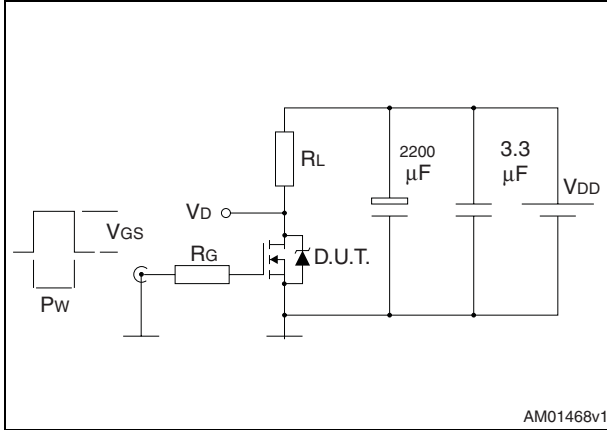
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-source breakdown voltage	$I_{gs} = \pm 1 \text{ mA}$ (open drain)	-30	-	30	V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

Test circuits

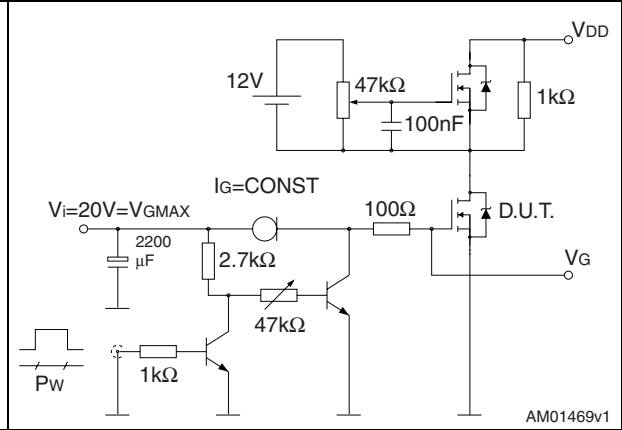
3 Test circuits

Figure 2. Switching times test circuit for resistive load



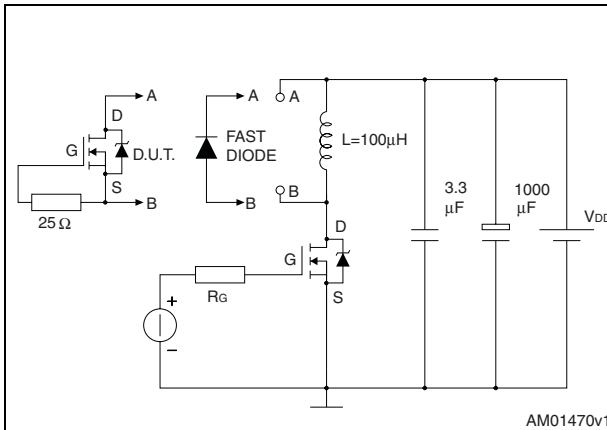
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Figure 3. Gate charge test circuit



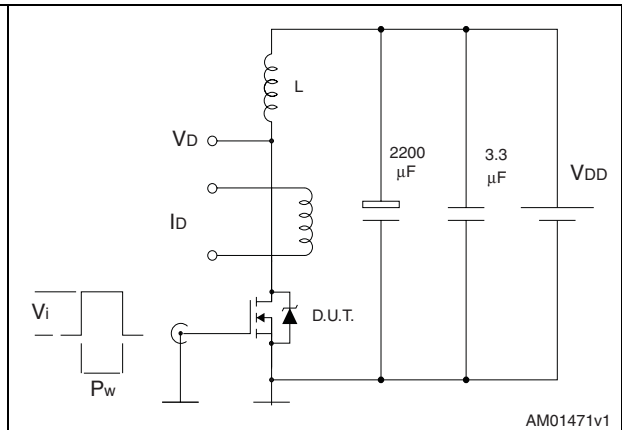
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Figure 4. Test circuit for inductive load switching and diode recovery times



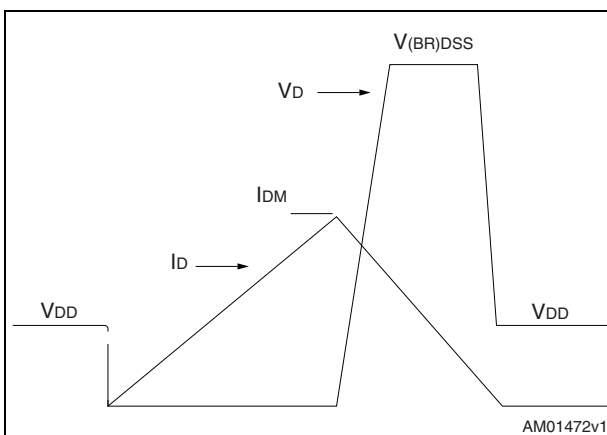
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Figure 5. Unclamped inductive load test circuit



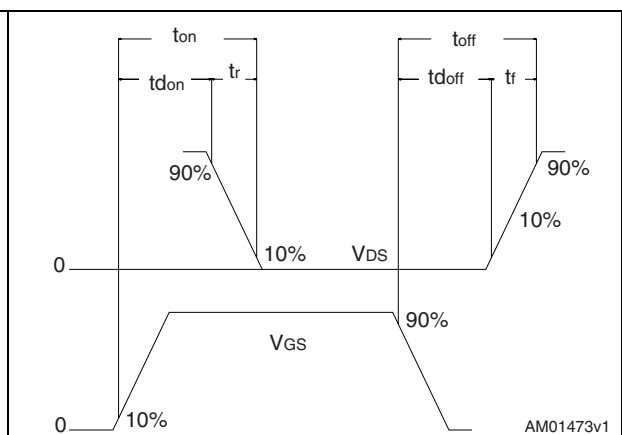
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Figure 6. Unclamped inductive waveform



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Figure 7. Switching time waveform



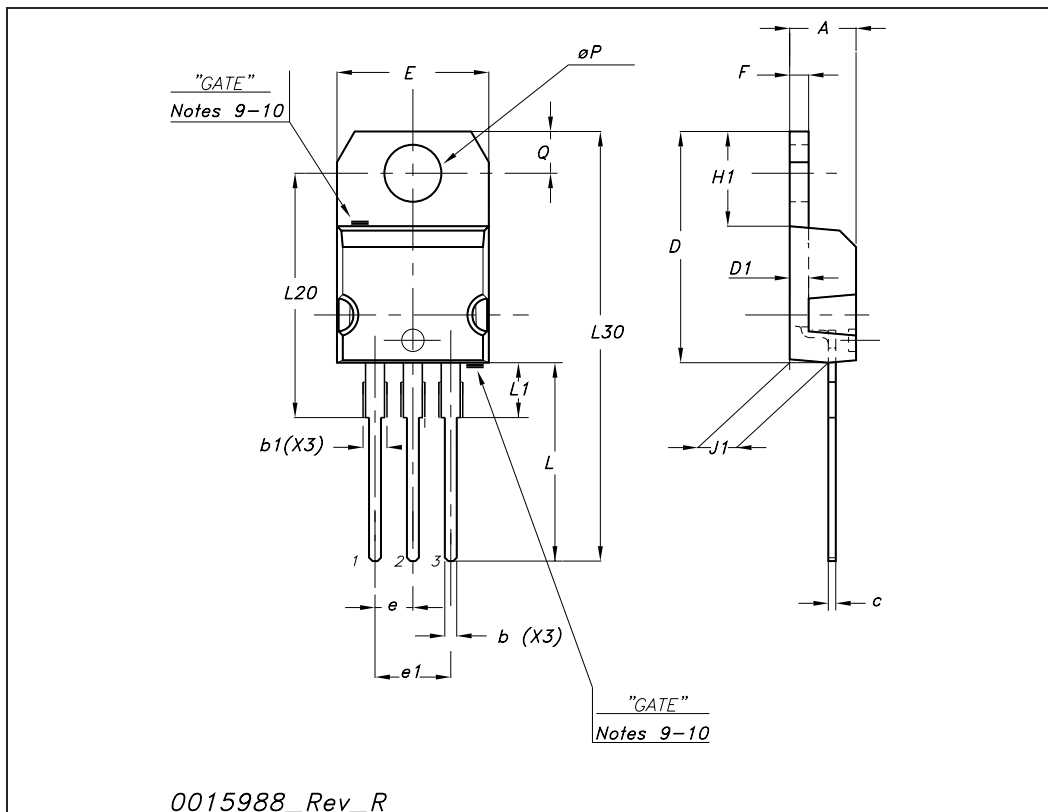
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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

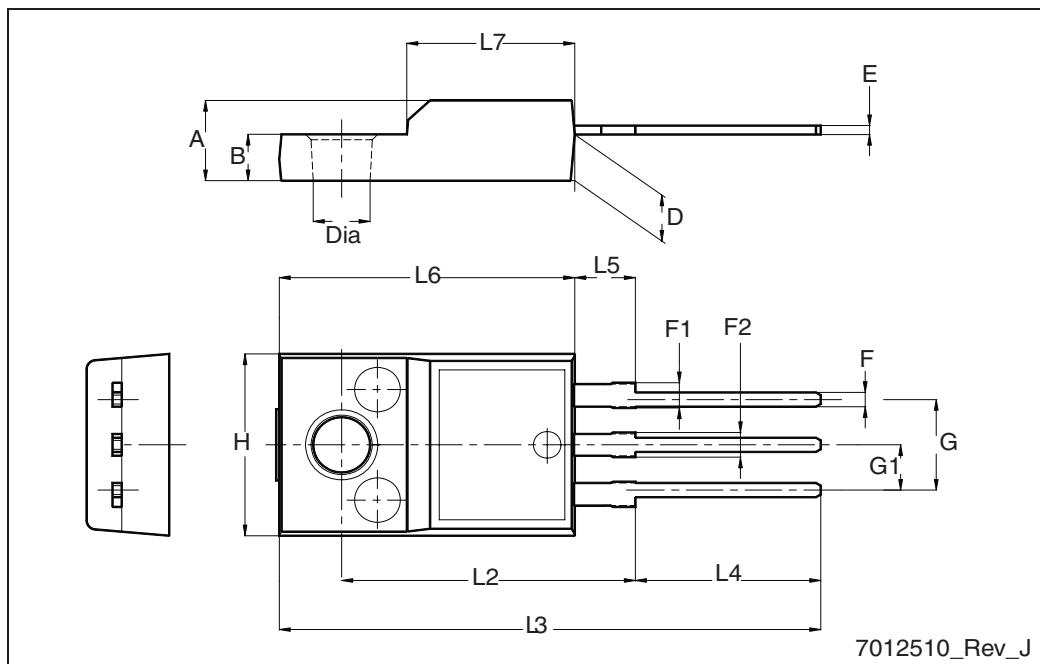
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
∅P	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



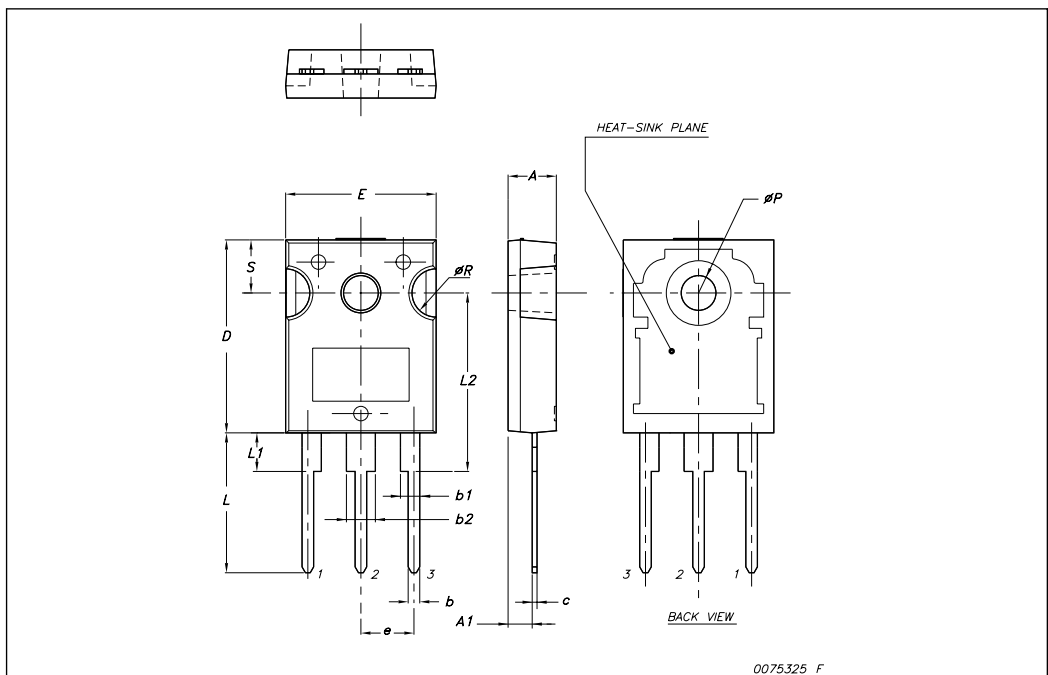
TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.5
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2



TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
15-May-2009	1	First release

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